

1. Material Substrate GaAs (N Type)
 Epitaxial Layer AlGaInP (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.7		V	IF=1mA
	$V_{F(2)}$		2.2	2.4	V	IF=20mA
Reverse Current	I_R			100	uA	VR=10V
Brightness	I_v	D	30	45	mcd	IF=20mA
		E	40	55		
		F	50	70		
Wavelength	λ_d		631		nm	IF=20mA
	$\Delta\lambda$		20		nm	IF=20mA

※ Note : Luminous Intensity is measured on bare chips.

4. Mechanical Data (a) Emission Area ----- 10mil x 10mil
 (b) Bottom Area ----- 11mil x 11mil
 (c) Bonding Pad ----- 130um
 (d) Chip Thickness ----- 11mil

